

Title (en)
SELF-PROTECT THYRISTOR

Title (de)
THYRISTOR MIT SELBSTSCHUTZ

Title (fr)
THYRISTOR A AUTO PROTECTION

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EP 0983613 A1 20000308 (DE)

Application
EP 98924147 A 19980418

Priority
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Abstract (en)
[origin: DE19721655C1] The invention relates to a self-protect thyristor with a series-located MOSFET (M1) and a second self-controlled MOSFET (M2) between the p base of the thyristor and the external cathode (KA). Said thyristor is provided with several parallel-connected unit cells for the thyristors in a semiconductor disk. The invention provides that the voltage in the series MOSFET (M1) should serve to indicate over-voltage and overheating. An additional MOSFET(M4) is also provided whose source (area) is connected to the source of the series MOSFET (M1) and whose gate is conductively connected to the drain of the series MOSFET (M1). The invention also includes resistor (Rg) between the gate electrode (G1) of the series MOSFET (M1) and the gate of the component.

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